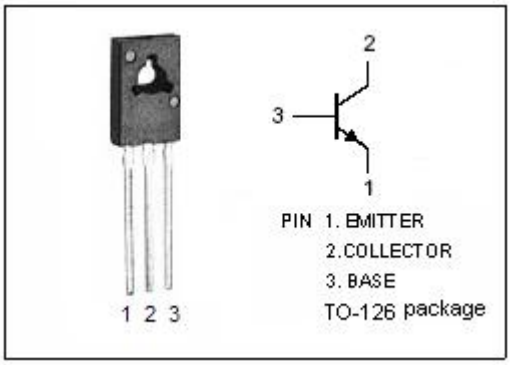
isc Silicon NPN Power Transistor — 2SC1567

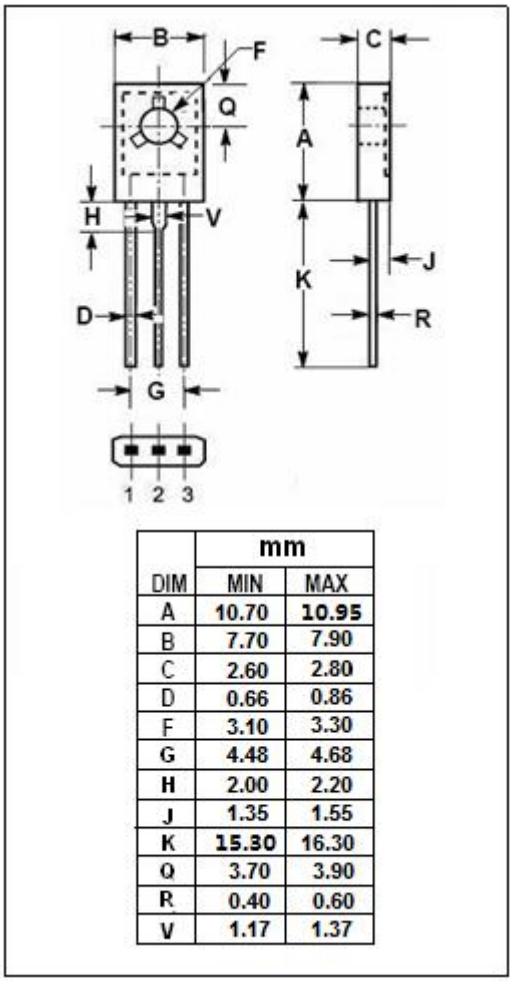
DESCRIPTION

- Collector-Emitter Breakdown Voltage
  : $V_{(BR)CEO}$= 100V(Min)
- Good Linearity of h_{FE}
- Complement to Type 2SA794
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for low-frequency high power driver.
- Optimum for the driver stage of low-frequency and 40W to 100W output amplifier.



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	0.5	A
I_{CP}	Collector Current-Peak	1	A
P_C	Collector Power Dissipation @ T_a=25℃	1.2	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-40~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 0.1mA ; I_B= 0	100			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Vltage	I_E= 1 μ A; I_C= 0	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 500mA; I_B= 50mA			0.4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 500mA; I_B= 50mA			1.2	V
h_{FE-1}	DC Current Gain	I_C= 150mA; V_{CE}= 10V	90		330	
h_{FE-2}	DC Current Gain	I_C= 500mA; V_{CE}= 5V	50			
f_T	Current-Gain—Bandwidth Product	I_E= -50mA ; V_{CB}= 10V		120		MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V,f_{test}= 1MHz		11		pF

◆ **h_{FE1} Classifications**

Q	R	S
90-155	130-220	185-330